# N-Channel 100-V (D-S) MOSFET

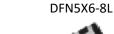
#### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- Low thermal impedance
- Fast switching speed

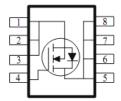
### **Typical Applications:**

- · LED Inverter Circuits
- DC/DC Conversion Circuits
- Motor drives

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)		
100	38 @ V <sub>GS</sub> = 10V	20 <sup>c</sup>		
	50 @ V <sub>GS</sub> = 4.5V	17 <sup>c</sup>		







ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Limit	Units			
Drain-Source Voltage			100	V		
Gate-Source Voltage			±20	V		
	T <sub>C</sub> =25°C		20 <sup>c</sup>	A		
Continuous Drain Current	T <sub>C</sub> =70°C	I <sub>D</sub>	16 <sup>c</sup>			
Continuous Drain Current	T <sub>A</sub> =25°C		9.4 <sup>a</sup>			
	T <sub>A</sub> =70°C		7.5 <sup>a</sup>			
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	30			
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	5.8			
	T <sub>C</sub> =25°C		23	W		
Power Dissipation	T <sub>C</sub> =70°C	$P_{D}$	15			
Fower Dissipation	T <sub>A</sub> =25°C	' D	5 <sup>a</sup>			
	T <sub>A</sub> =70°C		3.2 <sup>a</sup>			
Operating Junction and Storage Temperature Range		$T_J,T_stg$	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	D	25	°C/W		
IMAXIMUM JUNCTION-TO-Ambient	Steady State	$R_{\theta JA}$	65			
Maximum Junction-to-Case	Steady State	$R_{\theta JC}$	6			

#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature
- c. Package limited

#### **Electrical Characteristics**

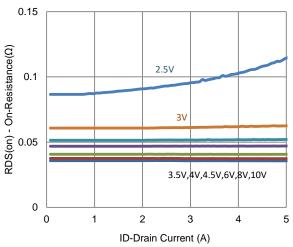
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zelo Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10		
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	15			Α	
Drain-Source On-Resistance <sup>a</sup>	r	$V_{GS} = 10 \text{ V}, I_{D} = 5 \text{ A}$			38	mΩ	
Drain-Source On-Resistance	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_{D} = 4 \text{ A}$			50		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15 \text{ V}, I_{D} = 5 \text{ A}$		12		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 2.9 \text{ A}, V_{GS} = 0 \text{ V}$		0.84		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	$Q_g$	$V_{DS} = 50 \text{ V}, V_{GS} = 4.5 \text{ V},$		6.2		nC	
Gate-Source Charge	$Q_gs$	$I_{DS} = 50 \text{ V}, V_{GS} = 4.3 \text{ V},$ $I_{D} = 5 \text{ A}$		2.3			
Gate-Drain Charge	$Q_gd$	1 <sub>D</sub> = 3 / X		2.9			
Turn-On Delay Time	$t_{d(on)}$	V 50 V D = 10 O		3			
Rise Time	t <sub>r</sub>	$V_{DS} = 50 \text{ V}, R_{L} = 10 \Omega,$ $I_{D} = 5 \text{ A},$		4		no	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		18		ns	
Fall Time	t <sub>f</sub>	V GEN = 10 V, T GEN 0 12		7			
Input Capacitance	C <sub>iss</sub>			404			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		87		pF	
Reverse Transfer Capacitance	$C_{rss}$			6			

#### Notes

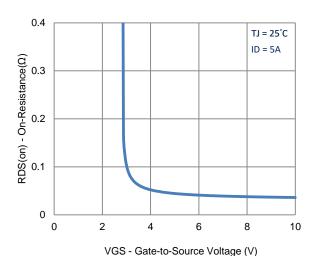
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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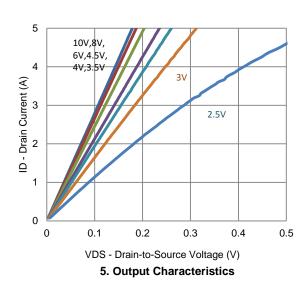
### **Typical Electrical Characteristics**

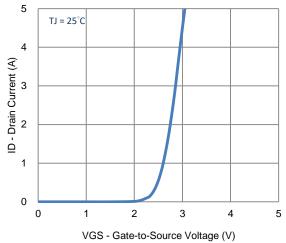


#### 1. On-Resistance vs. Drain Current

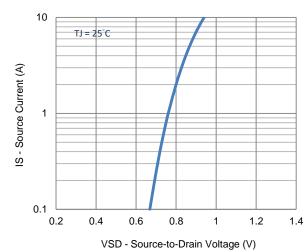


3. On-Resistance vs. Gate-to-Source Voltage

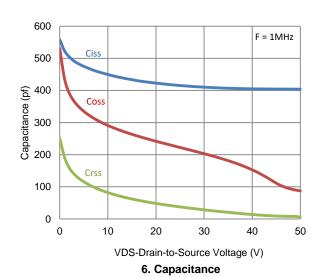




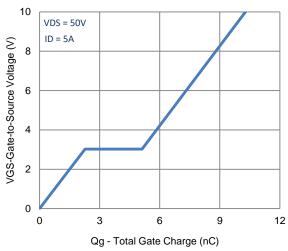
2. Transfer Characteristics



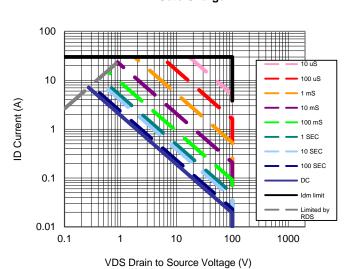
4. Drain-to-Source Forward Voltage



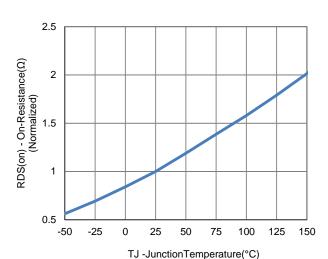
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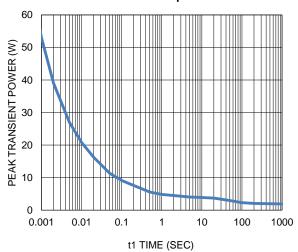




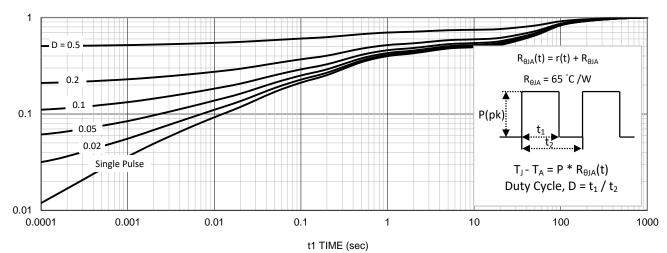
9. Safe Operating Area



8. Normalized On-Resistance Vs Junction Temperature

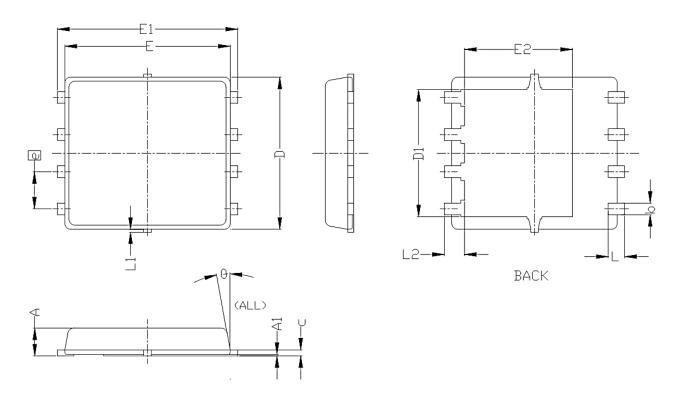


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

## **Package Information**



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.85	0.95	1.00	0.033	0.037	0.039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
С	0. 15	0.20	0. 25	0.006	0.008	0.010	
D	5. 20 BSC				0.205 BSC		
D1	4. 35 BSC				0. 171 BSC		
E	5, 55 BSC			0. 219 BSC			
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0. 050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0. 15	0		0.006	
L2	0.68 REF			0. 027 REF			
θ	0°		10°	0°		10°	